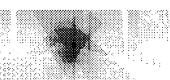




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Description

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(WO/2002/101841) III GROUP NITRIDE BASED SEMICONDUCTOR LUMINESCENT ELEMENT

National Phase

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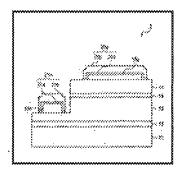
III GROUP NITRIDE BASED SEMICONDUCTOR LUMINESCENT ELEMENT

Abstract:

A III Group nitride based semiconductor luminescent element of flip

chip type, wherein a Au layer is provided via a Ti layer on the surface of a p-side electrode and the surface of an n-side

electrode.



Designated States:

AE, AG, AL, AM, AT, AU, AZ, BA, BB, BG, BR, BY, BZ, CA, CH, CN, CO, CR, CU, CZ, DE, DK, DM, DZ, EC, EE, ES, FI, GB, GD, GE, GH, GM, HR, HU, ID, IL, IN, IS, KE, KG, KP, KR, KZ, LC, LK, LR, LS, LT,

LU, LV, MA, MD, MG, MK, MN, MW, MX, MZ, NO, NZ, OM, PH, PL, PT, RO, RU, SD, SE, SG, SI, SK,

SL, TJ, TM, TN, TR, TT, TZ, UA, UG, US, UZ, VN, YU, ZA, ZM, ZW.

African Regional Intellectual Property Org. (ARIPO) (GH, GM, KE, LS, MW, MZ, SD, SL, SZ, TZ, UG,

Eurasian Patent Organization (EAPO) (AM, AZ, BY, KG, KZ, MD, RU, TJ, TM)

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